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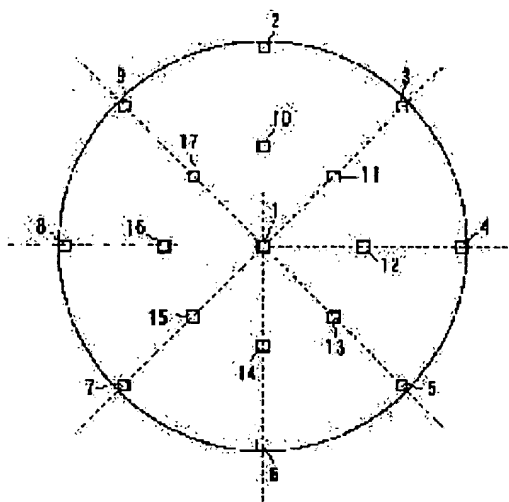
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(54) SPUTTERING TARGET, PRODUCTION METHOD THEREFOR AND ELECTRONIC PARTS

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a sputtering target in which particles and abnormal discharge generated on film deposition can be reduced to enable stable film deposition operation, and defects caused by particles, or the like, are reduced to improve the production yield of a semiconductor device, to provide a production method therefor, and to provide electronic parts.

SOLUTION: In the sputtering target, the average composition is expressed by the general formula of MS_x (wherein, M is at least one kind of metal selected from W, Mo, Ta, Ti and Nb and $2 \leq x \leq 4$ is satisfied). The target has a fine mixed structure in which metallic silicides are formed in a chainlike way, and further, an Si phase formed by the bonding of Si grains is discontinuously present on the gaps of the metallic silicides. The sputtering target contains at least either element selected from Au and Ag in the range of 10 to 300 ppm.



1~17 試料中の採取位置、測定位置

LEGAL STATUS

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